





Texas **INSTRUMENTS**

CD54HC166, CD54HCT166, CD74HC166, CD74HCT166 SCHS157D - FEBRUARY 1998 - REVISED FEBRUARY 2022

CDx4HC(T)166 High-Speed CMOS Logic 8-Bit Parallel-In/Serial-Out Shift Register

1 Features

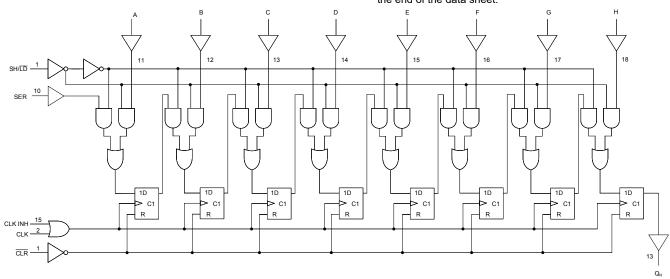
- **Buffered** inputs
- Fanout (over temperature range) •
 - Standard outputs: 10 LSTTL Loads
 - Bus driver outputs: 15 LSTTL Loads _
- Wide operating temperature range: -55°C to 125°C ٠
- Balanced propagation delay and transition time
- ٠ Significant power reduction compared to LSTTL Logic ICs
- HC Types
 - 2 V to 6 V operation
 - High noise immunity: $N_{II} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at V_{CC} = 5 V
- HCT Types
 - 4.5 V to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility,
 - $V_{IL} = 0.8V$ (Max), $V_{IH} = 2 V$ (Min)

2 Description

The 'HC166 and 'HCT166 8-bit shift register is fabricated with silicon gate CMOS technology. It possesses the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device.

Device Information									
PART NUMBER	BODY SIZE (NOM)								
CD54HC166F3A	CDIP (16)	24.38 mm × 6.92 mm							
CD54HCT166F3A	CDIP (16)	24.38 mm × 6.92 mm							
CD74HC166M	SOIC (16)	9.90 mm × 3.90 mm							
CD74HCT166M	SOIC (16)	9.90 mm × 3.90 mm							
CD74HC166E	PDIP (16)	19.31 mm × 6.35 mm							
CD74HCT166E	PDIP (16)	19.31 mm × 6.35 mm							

For all available packages, see the orderable addendum at (1)the end of the data sheet.



Functional Diagram





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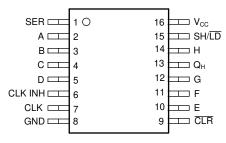
3 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision C (October 2003) to Revision D (February 2022)	Page
•	Updated the numbering, formatting, tables, figures and cross-references throughout the document to re	flect
	modern data sheet standards	1



4 Pin Configuration and Functions



J, N, or D package 16-Pin CDIP, PDIP, or SOIC Top View



5 Specifications

5.1 Absolute Maximum Ratings⁽¹⁾

			MIN	MAX	UNIT	
V _{CC}	Supply voltage	Supply voltage				
I _{IK}	Input diode current	For V_{I} < -0.5 V or V_{I} > VCC + 0.5 V		±20	mA	
I _{OK}	Output diode current	For V _O < -0.5 V or V _O > V _{CC} + 0.5 V		±20	mA	
lo	Drain current, per output	For -0.5 V < V _O < V _{CC} + 0.5 V		±25	mA	
I _O	Output source or sink current per output pin	For V _O > -0.5 V or V _O < V _{CC} + 0.5 V		±25	mA	
	Continuous current through V_{CC} or (GND		±50	mA	
TJ	Junction temperature			150	°C	
T _{stg}	Storage temperature range	Storage temperature range				
	Lead temperature (Soldering 10s)(S	OIC - lead tips only)		300	°C	

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 Recommended Operating Conditions

			MIN	MAX	UNIT
V _{CC}	Supply voltage range	HC Types		6	V
		HCT Types	4.5	5.5	V
V _I , V _O	Input or output voltage	0	V _{CC}	V	
		2V		1000	
tt	Input rise and fall time	4.5V		500	ns
		6V		400	
T _A	Temperature range		-55	125	C°

5.3 Thermal Information

			D (SOIC)	N (PDIP)	
Т	HERMAL METRI	C	16 PINS	16 PINS	UNIT
F	R _{0JA}	Junction-to-ambient thermal resistance ⁽¹⁾	73	67	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



5.4 Electrical Characteristics

	PARAMETER	TEST	Vcc	V _{CC} 25°C			-40°C to	85℃	-55°C to	UNIT	
		CONDITIONS ⁽²⁾	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
НС ТҮР	ES										
			2	1.5			1.5		1.5		V
V _{IH}	High level input voltage		4.5	3.15			3.15		3.15		V
	5		6	4.2			4.2		4.2		V
	1 I		2			0.5		0.5		0.5	V
V _{IL}	Low level input voltage		4.5			1.35		1.35		1.35	V
			6			1.8		1.8		1.8	V
	High level output	I _{OH} = – 20 μA	2	1.9			1.9		1.9		V
	voltage	I _{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
V _{OH}		I _{OH} = – 20 μA	6	5.9			5.9		5.9		V
	High level output	I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
	voltage	I _{OH} = – 5.2 mA	6	5.48			5.34		5.2		V
	Low level output	I _{OL} = 20 μA	2			0.1		0.1		0.1	V
	voltage	I _{OL} = 20 μA	4.5			0.1		0.1		0.1	V
V _{OL}		I _{OL} = 20 μA	6			0.1		0.1		0.1	V
	Low level output	I _{OL} = 4 mA	4.5			0.26		0.33		0.4	V
	voltage	I _{OL} = 5.2 mA	6			0.26		0.33		0.4	V
I _I	Input leakage current	$V_{I} = V_{CC}$ or GND	6			±0.1		±1		±1	μA
I _{CC}	Supply current	$V_{I} = V_{CC}$ or GND	6			8		80		160	μA
нст тү	PES										
V _{IH}	High level input voltage		4.5 to 5.5	2			2		2		V
V _{IL}	Low level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
N/	High level output voltage	I _{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
V _{OH}	High level output voltage	I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
	Low level output voltage	I _{OL} = 20 μA	4.5			0.1		0.1		0.1	V
V _{OL}	Low level output voltage	I _{OL} = 4 mA	4.5			0.26		0.33		0.4	V
I	Input leakage current	$V_{I} = V_{CC}$ or GND	5.5			±0.1		±1		±1	μΑ
I _{CC}	Supply current	$V_{I} = V_{CC}$ or GND	5.5			8		80		160	μA
		DS, D0-D7 inputs held at V _{CC} – 2.1 V	4.5 to 5.5		100	72		90		98	
ΔI _{CC} ⁽¹⁾	Additional supply current per input pin	\overline{PE} input held at V_{CC} – 2.1 V	4.5 to 5.5		100	126		157.5		171.5	μA
		CP, \overline{CE} inputs held at V _{CC} – 2.1 V	4.5 to 5.5		100	180		225		245	
		$\overline{\text{MR}}$ inputs held at $V_{\text{CC}} - 2.1 \text{ V}$	4.5 to 5.5		100	72		90		98	

(1) For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.



(2) $V_I = V_{IH}$ or V_{IL} , unless otherwise noted.

5.5 Prerequisite for Switching Characteristics

See (Parameter Measurement Information)

	PARAMETER	V _{cc} (V)	25°C		-40°C to 85°C		-55°C to 125°C		UNIT
	PARAMETER		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
НС ТҮР	ES			L.		•			
		2	6		5		4		MHz
f _{MAX}	Clock frequency	4.5	30		25		20		MHz
		6	35		29		23		MHz
		2	100		125		150		ns
t _w	MR pulse width	4.5	20		25		30		ns
		6	17		21		26		ns
		2	80		100		120		ns
t _W	Clock pulse width	4.5	16		20		24		ns
		6	14		17		20		ns
	Out and fine a	2	80		100		120		ns
t _{SU}	Set-up time Data and \overline{CE} to clock	4.5	16		20		24		ns
		6	14		17		20		ns
		2	1		1		1		ns
t _H	Hold time data to clock	4.5	1		1		1		ns
		6	1		1		1		ns
		2	0		0		0		ns
t _{REM}	Removal time \overline{MR} to clock	4.5	0		0		0		ns
		6	0		0		0		ns
		2	145		180		220		ns
t _{SU}	Set-up time \overline{PE} to CP	4.5	29		36		44		ns
		6	25		31		38		ns
		2	0		0		0		ns
t _H	Hold time \overline{PE} to CP or \overline{CE}	4.5	0		0		0		ns
		6	0		0		0		ns
НСТ ТҮ	PES	LL		k					
f _{MAX}	Clock frequency	4.5	25		20		16		MHz
t _w	MR pulse width	4.5	35		44		53		ns
t _w	Clock pulse width	4.5	20		25		30		ns
t _{SU}	Set-up time data and \overline{CE} to clock	4.5	16		20		24		ns
t _H	Hold time data to clock	4.5	0		0		0		ns
t _{REM}	Removal time MR to clock	4.5	0		0		0		ns
t _{SU}	Set-up time PE to CP	4.5	30		38		45		ns
t _H	Hold time \overline{PE} to CP or \overline{CE}	4.5	0		0		0		ns

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5.6 Switching Characteristics

Input t_r , $t_f = 6$ ns. Unless otherwise specified, $C_1 = 50$ pF. See (Parameter Measurement Information)

	PARAMETER	V _{cc} (V)	25°C		-40℃ to 85℃	-55°C to 125°C	UNIT	
			ТҮР	MAX	MAX	MAX		
НС ТҮРЕ	ES			I				
		2		160	200	240	ns	
t _{pd}	Clock to output	4.5	13 ⁽³⁾	32	40	48	ns	
		6		27	34	41	ns	
		2		75	95	110	ns	
tt	Output transition time	4.5		15	19	22	ns	
		6		13	16	19	ns	
		2		160	200	240	ns	
t _{PHL}	Propagation delay MR to output	4.5		32	40	48	ns	
		6		27	34	41	ns	
CI	Input capacitance			10	10	10	pF	
C _{PD}	Power dissipation capacitance ⁽¹⁾	5	41				pF	
НСТ ТҮР	PES			I		I		
t _{pd}	Clock to output	4.5		40	50	60	ns	
t _t	Output transition time	4.5		15	19	22	ns	
t _{PHL}	Propagation delay MR to output	4.5		40	50	60	ns	
CI	Input capacitance			10	10	10	pF	

(1)

 C_{PD} is used to determine the dynamic power consumption, per gate. $P_D = C_{PD} V_{CC} {}^2f_i + \Sigma (C_L V_{CC} {}^2 + f_0)$ where f_i = Input Frequency, f_0 = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply (2) Voltage.

(3) $C_L = 15$ and $V_{CC} = 5$ V.



 V_{CC}

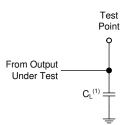
V_{OH}

6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 6 ns.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.



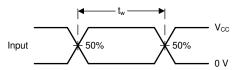


Figure 6-2. Voltage Waveforms, Standard CMOS **Inputs Pulse Duration**

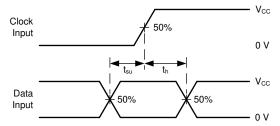


Figure 6-3. Voltage Waveforms, Standard CMOS **Inputs Setup and Hold Times**

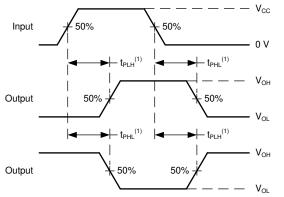
90%

10% t.(1

909

90%

Input





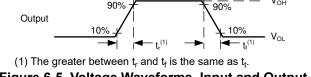
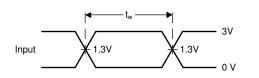


Figure 6-5. Voltage Waveforms, Input and Output **Transition Times for Standard CMOS Input Devices**







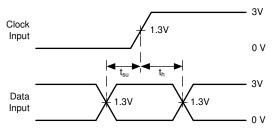
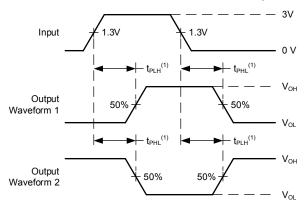


Figure 6-7. Voltage Waveforms, TTL-Compatible CMOS Inputs Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as $t_{\mathsf{pd}}.$

Figure 6-8. Voltage Waveforms, TTL-Compatible CMOS Inputs Propagation Delays



7 Detailed Description

7.1 Overview

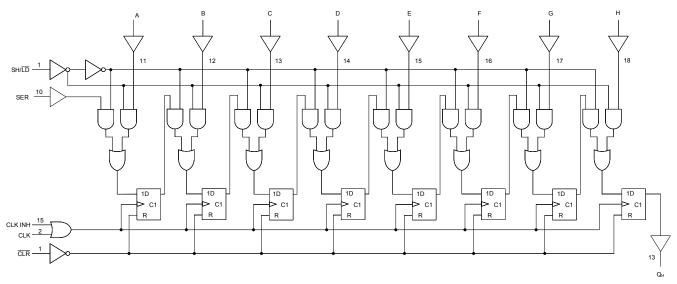
The 'HC166 and 'HCT166 8-bit shift register is fabricated with silicon gate CMOS technology. It possesses the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device.

The 'HCT166 is functionally and pin compatible with the standard 'LS166.

The 166 is an 8-bit shift register that has fully synchronous serial or parallel data entry selected by an active LOW Parallel Enable (\overline{PE}) input. When the \overline{PE} is LOW one setup time before the LOW-to-HIGH clock transition, parallel data is entered into the register. When \overline{PE} is HIGH, data is entered into the internal bit position Q0 from Serial Data Input (DS), and the remaining bits are shifted one place to the right (Q0 \rightarrow Q1 \rightarrow Q2, etc.) with each positive-going clock transition. For expansion of the register in parallel to serial converters, the Q7 output is connected to the DS input of the succeeding stage.

The clock input is a gated OR structure which allows one input to be used as an active LOW Clock Enable (\overline{CE}) input. The pin assignment for the CP and \overline{CE} inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of \overline{CE} input should only take place while the CP is HIGH for predictable operation.

A LOW on the Controller Reset (\overline{MR}) input overrides all other inputs and clears the register asynchronously, forcing all bit positions to a LOW state.



7.2 Functional Block Diagram



7.3 Device Functional Modes

		INTE	OUTPUT					
MASTER	PARALLEL	CLOCK	CLOCK	SERIAL -	PARALLEL	Q ST.	OUTPUT Q7	
RESET	ENABLE	ENABLE	CLOCK		D0 D7	Q0	Q1	
L	X	Х	Х	Х	Х	L	L	L
н	Х	L	L	Х	Х	Q00	Q10	Q0
Н	L	L	1	Х	ah	а	b	h
Н	Н	L	1	Н	Х	Н	Q0n	Q6n
Н	Н	L	↑	L	Х	L	Q0n	Q6n
Н	Х	Н	1	Х	Х	Q00	Q10	Q70

Table 7-1. Truth Table⁽¹⁾

(1) H = High Voltage Level,

L = Low Voltage Level,

X = Don't Care,

 \uparrow = Transition from Low to High Level,

a...h = The level of steady-state input at inputs D0 thru D7, respectively,

Q00, Q10, Q70 = The level of Q0, Q1, or Q7, respectively, before the indicated steady-state input conditions were established Q0n, Q6n = The level of Q0 or Q6, respectively, before the most recent ↑ transition of the clock.



8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(1)				-	(_/	(6)	(-)		(
CD54HC166F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC166F3A	Samples
CD54HCT166F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT166F3A	Samples
CD74HC166E	ACTIVE	PDIP	Ν	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC166E	Samples
CD74HC166M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	HC166M	Samples
CD74HCT166E	ACTIVE	PDIP	Ν	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT166E	Samples
CD74HCT166EE4	ACTIVE	PDIP	Ν	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT166E	Samples
CD74HCT166M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	HCT166M	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



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PACKAGE OPTION ADDENDUM

11-May-2023

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD54HC166, CD54HC166, CD74HC166, CD74HC166; :

- Catalog : CD74HC166, CD74HCT166
- Military : CD54HC166, CD54HCT166

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



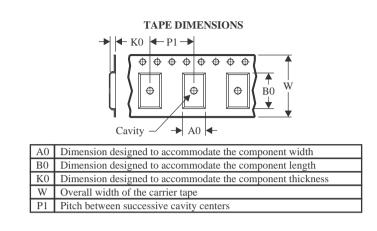
Texas

*All dimensions are nominal

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC166M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HC166M96	SOIC	D	16	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
CD74HCT166M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HCT166M96	SOIC	D	16	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC166M96	SOIC	D	16	2500	356.0	356.0	35.0
CD74HC166M96	SOIC	D	16	2500	366.0	364.0	50.0
CD74HCT166M96	SOIC	D	16	2500	356.0	356.0	35.0
CD74HCT166M96	SOIC	D	16	2500	366.0	364.0	50.0

TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166EE4	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166EE4	N	PDIP	16	25	506	13.97	11230	4.32

J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



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